



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of:
David J. Keller

Serial No.: 09/458,875

Filed: December 10, 1999

For: **POLYSILICON ETCH USEFUL DURING THE
MANUFACTURE OF A SEMICONDUCTOR
DEVICE**

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§ GAU: 1763
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§ Examiner: George Goudreau
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§ Atty. Docket: 99-0738.00
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Commissioner for Patents
Washington, D.C. 20231

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October 16, 2002

Date

Signature

RESPONSE TO THE OFFICE ACTION OF JULY 16, 2002

In response to the final office action of July 16, 2002, please amend the application as indicated below.

In the Claims

Prior to examining the above-captioned application, please add the following new claims as set forth below then cancel all of pending claims 1-19, 21-23, and 25-26 without prejudice.

-- 27. A method used to form a semiconductor device, comprising:

providing a semiconductor wafer substrate assembly having at least first and second features in spaced relation to each other which define a region comprising an opening between said first and second features;

forming a conductive layer over said first and second features and within said opening;